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2N5195 Silicon PNP Transistor Audio Power Amp, Switch TO-126 Type Package

Description:

The 2N5195 is a silicon PNP transistor in a TO-126 plastic package designed for use in power amplifier and switching circuits.

Features:

- Excellent Safe Area Limits

Absolute Maximum Ratings:

Collector-Emitter Voltage, V_{CEO}	80V
Collector-Base Voltage, V_{CB}	80V
Emitter-Base Voltage, V_{EB}	5V
Collector Current, I_C	4A
Base Current, I_B	1A
Total Power Dissipation ($T_C = +25^\circ\text{C}$), P_D	40W
Derate Above 25°C	320mW/ $^\circ\text{C}$
Operating Junction Temperature Range, T_J	-65° to $+150^\circ\text{C}$
Storage Temperature Range, T_{stg}	-65° to $+150^\circ\text{C}$
Thermal Resistance, Junction-to-Case, R_{thJC}	3.12°C/W

Electrical Characteristics: ($T_C = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF Characteristics						
Collector-Emitter Sustaining Voltage	$V_{CEO(sus)}$	$I_C = 0.1\text{A}, I_B = 0$, Note 1	80	-	-	V
Collector Cutoff Current	I_{CEO}	$V_{CE} = 80\text{V}, I_B = 0$	-	-	1.0	mA
	I_{CEX}	$V_{CE} = 80\text{V}, V_{EB(off)} = 1.5\text{V}$	-	-	0.1	mA
		$V_{CE} = 80\text{V}, V_{EB(off)} = 1.5\text{V}, T_C = +150^\circ\text{C}$	-	-	2.0	mA
	I_{CBO}	$V_{CB} = 80\text{V}, I_E = 0$	-	-	0.1	mA
Emitter Cutoff Current	I_{EBO}	$V_{BE} = 5\text{V}, I_C = 0$	-	-	1.0	mA

Electrical Characteristics: ($T_C = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
ON Characteristics (Note 1)						
DC Current Gain	h_{FE}	$I_C = 1.5\text{A}, V_{CE} = 2\text{V}$	20	-	80	
		$I_C = 4\text{A}, V_{CE} = 2\text{V}$	7	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 1.5\text{A}, I_B = 0.15\text{A}$	-	-	0.6	V
		$I_C = 4\text{A}, I_B = 1\text{A}$	-	-	1.4	V
Base-Emitter ON Voltage	$V_{BE(on)}$	$I_C = 1.5\text{A}, V_{CE} = 2\text{V}$	-	-	1.2	V
Dynamic Characteristics						
Current Gain-Bandwidth Product	f_T	$I_C = 1\text{A}, V_{CE} = 10\text{V}, f = 1\text{MHz}$	2.0	-	-	MHz

Note 1. Pulse test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.

